

- **768 × 1 Sensor-Element Organization**
- **400 Dot-Per-Inch (DPI) Sensor Pitch**
- **High Linearity and Uniformity**
- **Wide Dynamic Range . . . 4000:1 (72 dB)**
- **Output Referenced to Ground**
- **Low Image Lag . . . 0.5% Typ**
- **Operation to 8 MHz**
- **Single 3-V to 5-V Supply**
- **Rail-to-Rail Output Swing (AO)**
- **No External Load Resistor Required**
- **Replacement for TSL1406**

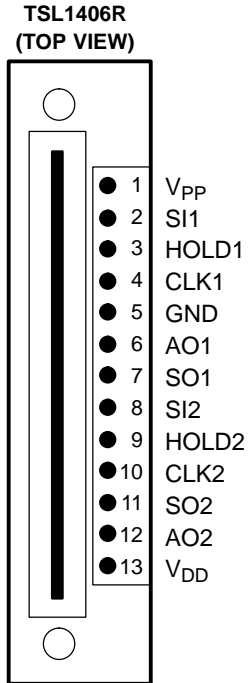
Description

The TSL1406R is a 400 dots-per-inch (DPI) linear sensor array consisting of two 384-pixel sections, each with its own output. The sections are aligned to form a contiguous 768 × 1 pixel array. The device incorporates a pixel data-hold function that provides simultaneous integration-start and integration-stop times for all pixels.

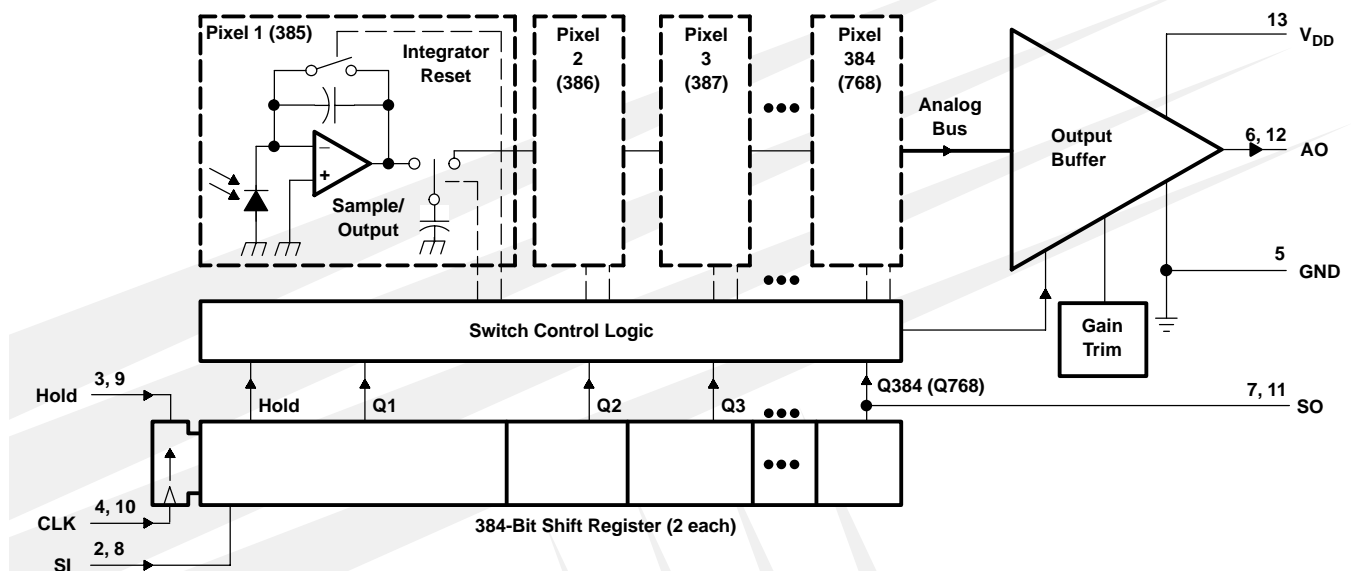
Pixels measure 63.5 μm by 55.5 μm, with 63.5-μm center-to-center spacing and 8-μm spacing between pixels. Operation is simplified by internal logic that requires only a serial-input (SI) pulse and a clock.

The device operates from a single 5-V power source. The two sections of 384 pixels each can be read out separately or can be cascaded to provide a single output for all 768 pixels (see Figure 9).

The TSL1406RS is the same device mounted in a shorter package. These devices are intended for use in a wide variety of applications including mark and code reading, OCR and contact imaging, edge detection and positioning, and optical encoding.



Functional Block Diagram (each section)



TSL1406R, TSL1406RS

768 × 1 LINEAR SENSOR ARRAY WITH HOLD

TAOS042B – MAY 2004

Terminal Functions

TERMINAL NAME	NO.	I/O	DESCRIPTION
AO1	6	O	Analog output, section 1.
AO2	12	O	Analog output, section 2.
CLK1	4	I	Clock, section 1. CLK1 controls charge transfer, pixel output, and reset.
CLK2	10	I	Clock, section 2. CLK2 controls charge transfer, pixel output, and reset.
GND	5		Ground (substrate). All voltages are referenced to GND.
HOLD1	3	I	Hold signal. HOLD1 shifts pixel data to parallel buffer. HOLD1 is normally connected to SI1 and HOLD2 in serial mode, SI1 in parallel mode.
HOLD2	9	I	Hold signal. HOLD2 shifts pixel data to parallel buffer. HOLD2 is normally connected to SI2 in parallel mode.
SI1	2	I	Serial input (section 1). SI1 defines the start of the data-out sequence.
SI2	8	I	Serial input (section 2). SI2 defines the start of the data-out sequence.
SO1	7	O	Serial output (section 1). SO1 provides a signal to drive the SI2 input in serial mode.
SO2	11	O	Serial output (section 2). SO2 provides a signal to drive the SI input of another device for cascading or as an <i>end-of-data</i> indication.
V _{DD}	13		Supply voltage for both analog and digital circuitry.
V _{PP}	1		Normally grounded.

Detailed Description

The sensor consists of 768 photodiodes, called pixels, arranged in a linear array. Light energy impinging on a pixel generates photocurrent that is then integrated by the active integration circuitry associated with that pixel.

During the integration period, a sampling capacitor connects to the output of the integrator through an analog switch. The amount of charge accumulated at each pixel is directly proportional to the light intensity on that pixel and the integration time.

The output and reset of the integrators are controlled by a 384-bit shift register and reset logic. An output cycle is initiated by clocking in a logic 1 on SI. Another signal, called HOLD, is generated from the rising edge of SI1 when SI1 and HOLD1 are connected together. This causes all 384 sampling capacitors to be disconnected from their respective integrators and starts an integrator reset period. As the SI pulse is clocked through the shift register, the charge stored on the sampling capacitors is sequentially connected to a charge-coupled output amplifier that generates a voltage on analog output AO. The integrator reset period ends 18 clock cycles after the SI pulse is clocked in. Then the next integration period begins. On the 384th clock rising edge, the SI pulse is clocked out on the SO1 pin (section 1) and becomes the SI pulse for section 2 (when SO1 is connected to SI2). The rising edge of the 385th clock cycle terminates the SO1 pulse, and returns the analog output AO of section 1 to high-impedance state. Similarly, SO2 is clocked out on the 768th clock pulse. Note that a 769th clock pulse is needed to terminate the SO2 pulse and return AO of Section 2 to the high-impedance state. If a minimum integration time is desired, the next SI pulse may be presented after a minimum delay of t_{qt} (pixel charge transfer time) after the 769th clock pulse. Sections 1 and 2 may be operated in parallel or in serial fashion.

AO is an op amp-type output that does not require an external pull-down resistor. This design allows a rail-to-rail output voltage swing. With $V_{DD} = 5\text{ V}$, the output is nominally 0 V for no light input, 2 V for normal white level, and 4.8 V for saturation light level. When the device is not in the output phase, AO is in a high-impedance state.

The voltage developed at analog output (AO) is given by:

$$V_{out} = V_{drk} + (R_e)(E_e)(t_{int})$$

where:

V_{out}	is the analog output voltage for white condition
V_{drk}	is the analog output voltage for dark condition
R_e	is the device responsivity for a given wavelength of light given in $V/(\mu\text{J}/\text{cm}^2)$
E_e	is the incident irradiance in $\mu\text{W}/\text{cm}^2$
t_{int}	is integration time in seconds

A 0.1 μF bypass capacitor should be connected between V_{DD} and ground as close as possible to the device.

TSL1406R, TSL1406RS

768 × 1 LINEAR SENSOR ARRAY WITH HOLD

TAOS042B – MAY 2004

Absolute Maximum Ratings†

Supply voltage range, V_{DD}	–0.3 V to 6 V
Input voltage range, V_I	–0.3 V to $V_{DD} + 0.3$ V
Input clamp current, I_{IK} ($V_I < 0$) or ($V_I > V_{DD}$)	–20 mA to 20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{DD}$)	–25 mA to 25 mA
Voltage range applied to any output in the high impedance or power-off state, V_O	–0.3 V to $V_{DD} + 0.3$ V
Continuous output current, I_O ($V_O = 0$ to V_{DD})	–25 mA to 25 mA
Continuous current through V_{DD} or GND	–40 mA to 40 mA
Analog output current range, I_O	–25 mA to 25 mA
Maximum light exposure at 638 nm	5 mJ/cm ²
Operating free-air temperature range, T_A	0°C to 70°C
Storage temperature range, T_{stg}	–25°C to 85°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “Recommended Operating Conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Recommended Operating Conditions (see Figure 1 and Figure 2)

	MIN	NOM	MAX	UNIT
Supply voltage, V_{DD}	3	5	5.5	V
Input voltage, V_I	0		V_{DD}	V
High-level input voltage, V_{IH}	2		V_{DD}	V
Low-level input voltage, V_{IL}	0		0.8	V
Wavelength of light source, λ	400		1000	nm
Clock frequency, f_{clock}	5		8000	kHz
Sensor integration time, Serial, t_{int} (see Note 1)	0.11375		100	ms
Sensor integration time, Parallel, t_{int} (see Note 1)	0.06575		100	ms
Setup time, serial input, $t_{su(SI)}$	20			ns
Hold time, serial input, $t_{h(SI)}$ (see Note 2)	0			ns
Operating free-air temperature, T_A	0		70	°C

NOTES: 1. Integration time is calculated as follows:

$$t_{int} = (768 - 18) \times \text{clock period} + 20 \mu\text{s}$$

where 768 is the number of pixels in series, 18 is the required logic setup clocks, and 20 μs is the pixel charge transfer time (t_{qt})

2. SI must go low before the rising edge of the next clock pulse.

Electrical Characteristics at $f_{\text{clock}} = 1 \text{ MHz}$, $V_{\text{DD}} = 5 \text{ V}$, $T_{\text{A}} = 25^{\circ}\text{C}$, $\lambda_{\text{p}} = 640 \text{ nm}$, $t_{\text{int}} = 5 \text{ ms}$, $R_{\text{L}} = 330 \Omega$, $E_{\text{e}} = 12.5 \mu\text{W}/\text{cm}^2$ (unless otherwise noted) (see Note 3)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{out}	Analog output voltage (white, average over 768 pixels)	See Note 4	1.6	2	2.4	V
V _{drk}	Analog output voltage (dark, average over 256 pixels)	E _e = 0	0	0.1	0.3	V
PRNU	Pixel response nonuniformity	See Note 5	±15%			
	Nonlinearity of analog output voltage	See Note 6	0.4%			FS
	Output noise voltage	See Note 7	1			mVrms
R _e	Responsivity	See Note 8	20	30	38	V/ (μJ/cm ²)
V _{sat}	Analog output saturation voltage	V _{DD} = 5 V, R _L = 330 Ω	4.5	4.8		V
		V _{DD} = 3 V, R _L = 330 Ω	2.5	2.8		
SE	Saturation exposure	V _{DD} = 5 V, See Note 9	155			nJ/cm ²
		V _{DD} = 3 V, See Note 9	90			
DSNU	Dark signal nonuniformity	All pixels, E _e = 0, See Note 10	0.05	0.15		V
IL	Image lag	See Note 11	0.5%			
I _{DD}	Supply current	V _{DD} = 5 V, E _e = 0, R _L = 330 Ω	18	27		mA
		V _{DD} = 3 V, E _e = 0, R _L = 330 Ω	16	25		
I _{IH}	High-level input current	V _I = V _{DD}	10			μA
I _{IL}	Low-level input current	V _I = 0	10			μA
C _i	Input capacitance, SI		15			pF
C _i	Input capacitance, CLK		30			pF

- NOTES: 3. All measurements made with a 0.1 μF capacitor connected between V_{DD} and ground.
4. The array is uniformly illuminated with a diffused LED source having a peak wavelength of 640 nm.
5. PRNU is the maximum difference between the voltage from any single pixel and the average output voltage from all pixels of the device under test when the array is uniformly illuminated.
6. Nonlinearity is defined as the maximum deviation from a best-fit straight line over the dark-to-white irradiance levels, as a percent of analog output voltage (white).
7. RMS noise is the standard deviation of a single-pixel output under constant illumination as observed over a 5-second period.
8. $R_{\text{e}}(\text{min}) = [V_{\text{out}}(\text{min}) - V_{\text{drk}}(\text{max})] \div (E_{\text{e}} \times t_{\text{int}})$
9. $\text{SE}(\text{min}) = [V_{\text{sat}}(\text{min}) - V_{\text{drk}}(\text{min})] \times (E_{\text{e}} \times t_{\text{int}}) \div [V_{\text{out}}(\text{max}) - V_{\text{drk}}(\text{min})]$
10. DSNU is the difference between the maximum and minimum output voltage for all pixels in the absence of illumination.
11. Image lag is a residual signal left in a pixel from a previous exposure. It is defined as a percent of white-level signal remaining after a pixel is exposed to a white condition followed by a dark condition:

$$\text{IL} = \frac{V_{\text{out}}(\text{IL}) - V_{\text{drk}}}{V_{\text{out}}(\text{white}) - V_{\text{drk}}} \times 100$$

Timing Requirements (see Figure 1 and Figure 2)

	MIN	NOM	MAX	UNIT
$t_{\text{su}}(\text{SI})$ Setup time, serial input (see Note 12)	20			ns
$t_{\text{h}}(\text{SI})$ Hold time, serial input (see Note 12 and Note 13)	0			ns
$t_{\text{pd}}(\text{SO})$ Propagation delay time, SO		50		ns
t_{w} Pulse duration, clock high or low	50			ns
t_{r} , t_{f} Input transition (rise and fall) time	0		500	ns
t_{qt} Pixel charge transfer time	20			μs

- NOTES: 12. Input pulses have the following characteristics: $t_{\text{r}} = 6 \text{ ns}$, $t_{\text{f}} = 6 \text{ ns}$.
13. SI must go low before the rising edge of the next clock pulse.

TSL1406R, TSL1406RS

768 × 1 LINEAR SENSOR ARRAY WITH HOLD

TAOS042B – MAY 2004

Dynamic Characteristics over recommended ranges of supply voltage and operating free-air temperature (see Figures 7 and 8)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_s Analog output settling time to $\pm 1\%$	$R_L = 330 \Omega$, $C_L = 50 \text{ pF}$		120		ns
$t_{pd(SO)}$ Propagation delay time, SO1, SO2			50		ns

TYPICAL CHARACTERISTICS

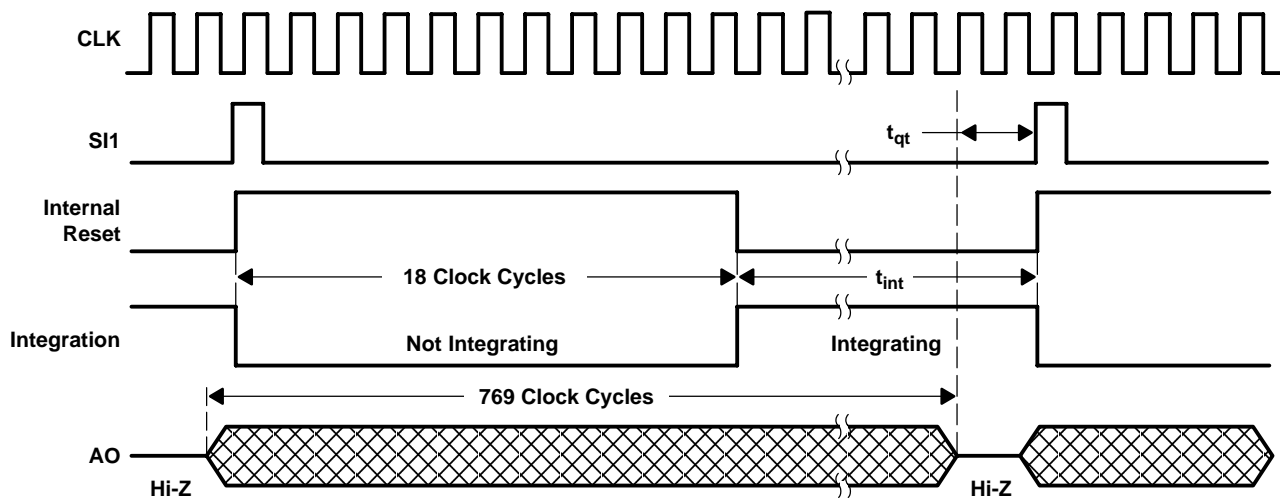


Figure 1. Timing Waveforms (serial connection)

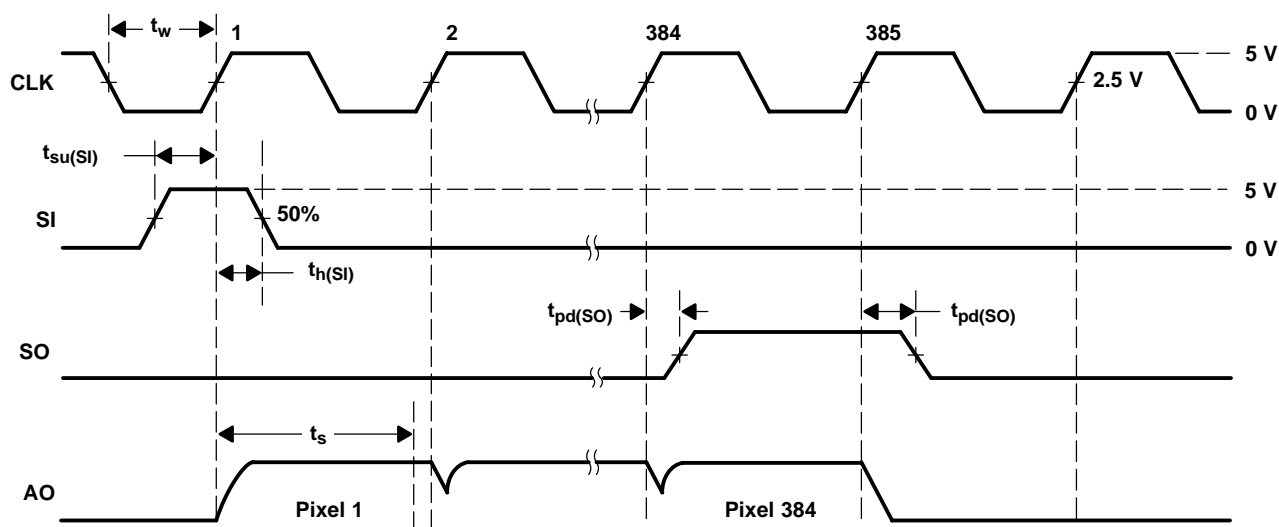


Figure 2. Operational Waveforms (each section)



TYPICAL CHARACTERISTICS

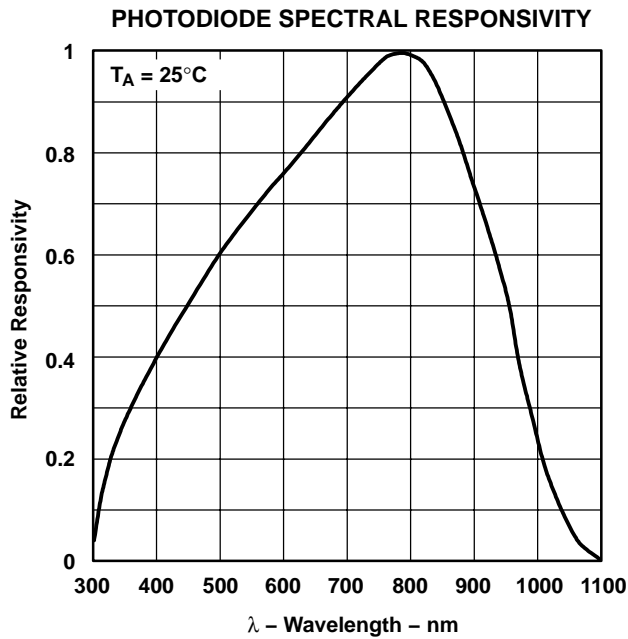


Figure 3

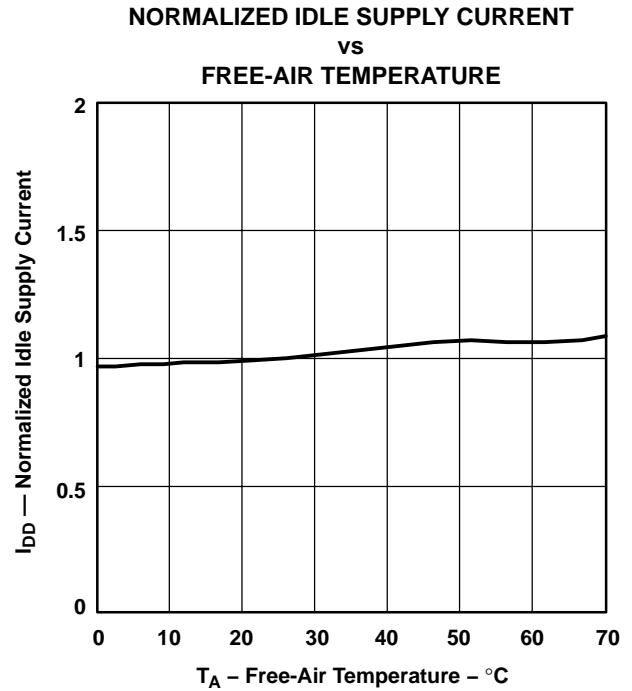


Figure 4

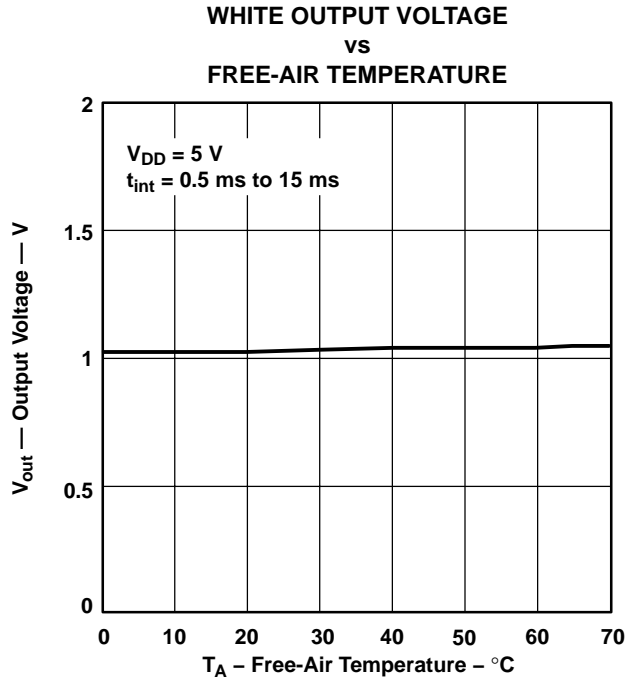


Figure 5

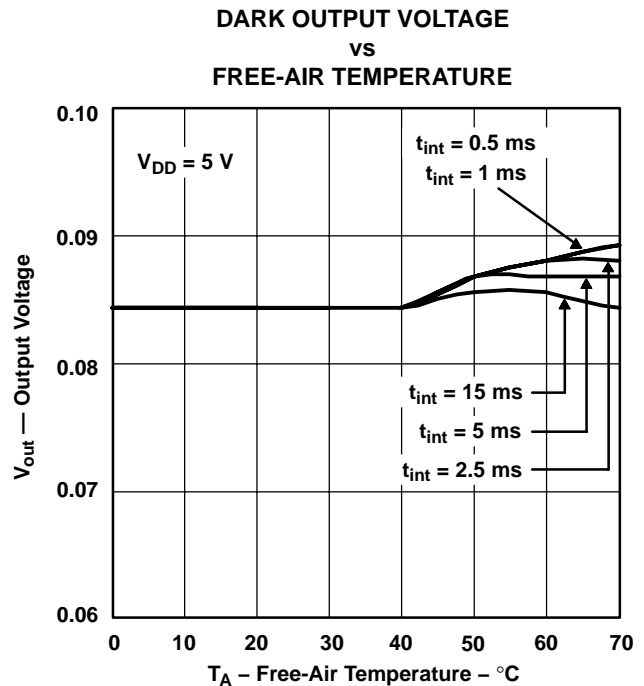


Figure 6

TSL1406R, TSL1406RS

768 × 1 LINEAR SENSOR ARRAY WITH HOLD

TAOS042B – MAY 2004

TYPICAL CHARACTERISTICS

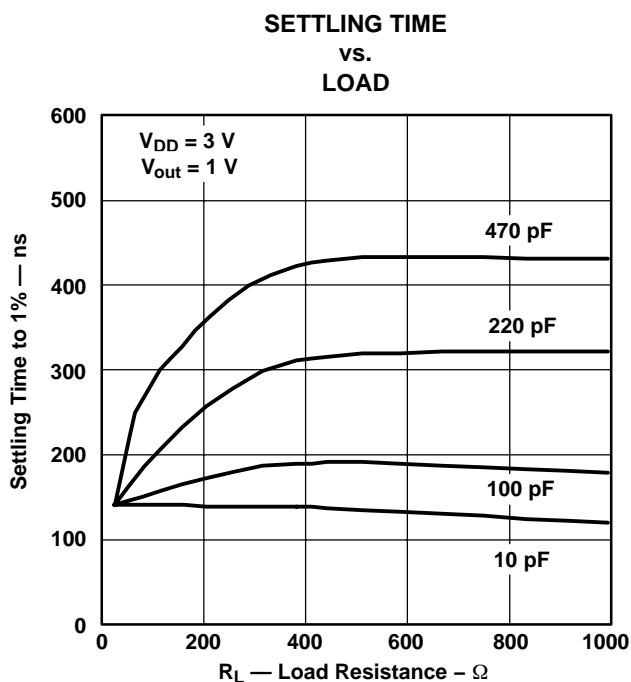


Figure 7

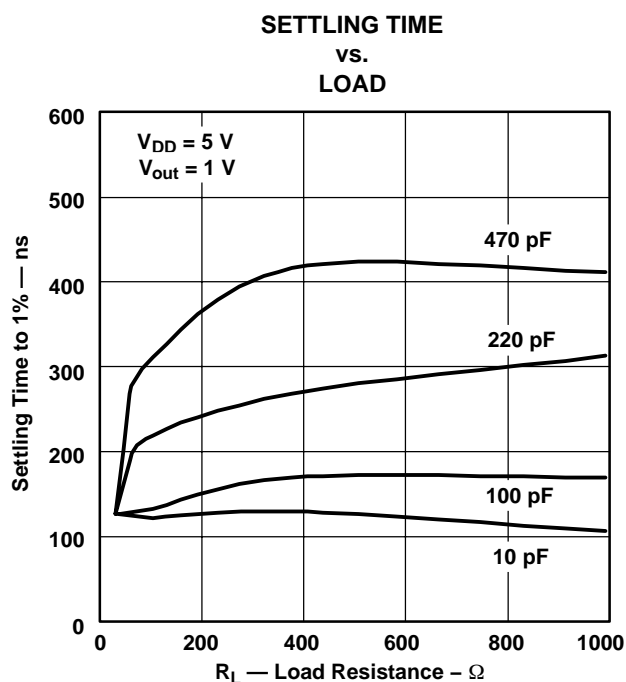


Figure 8

APPLICATION INFORMATION

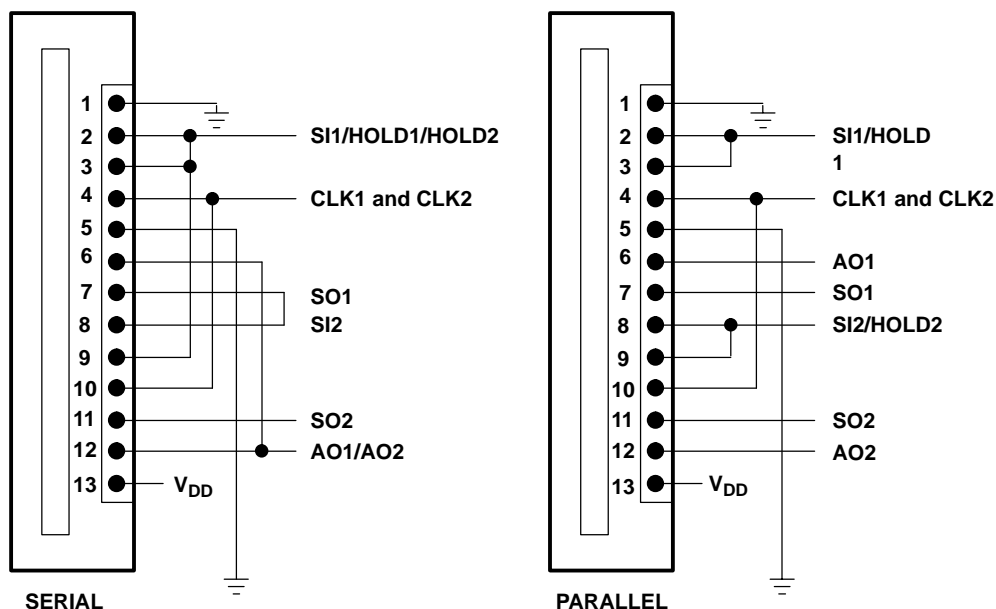
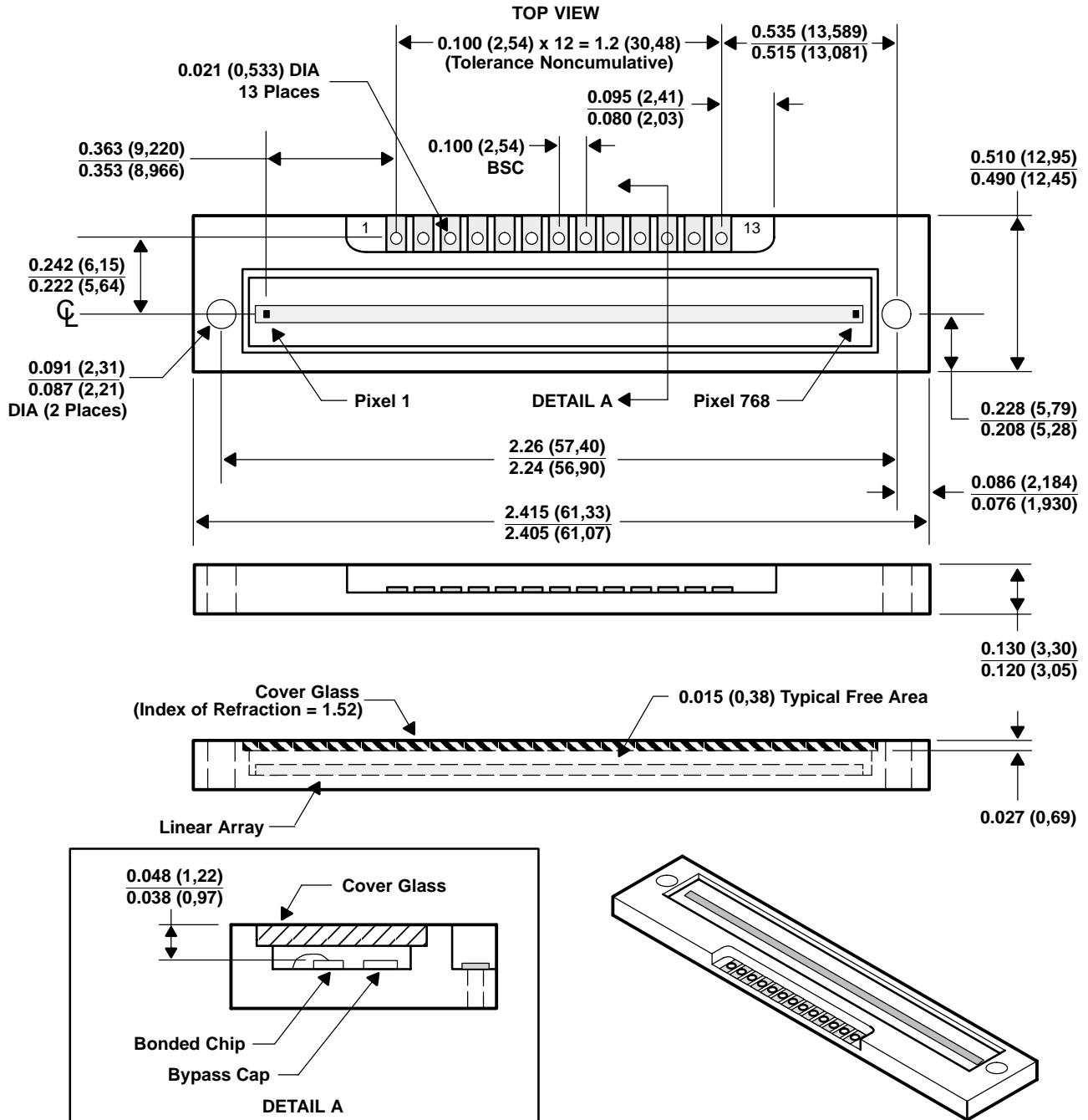


Figure 9. Operational Connections



MECHANICAL DATA

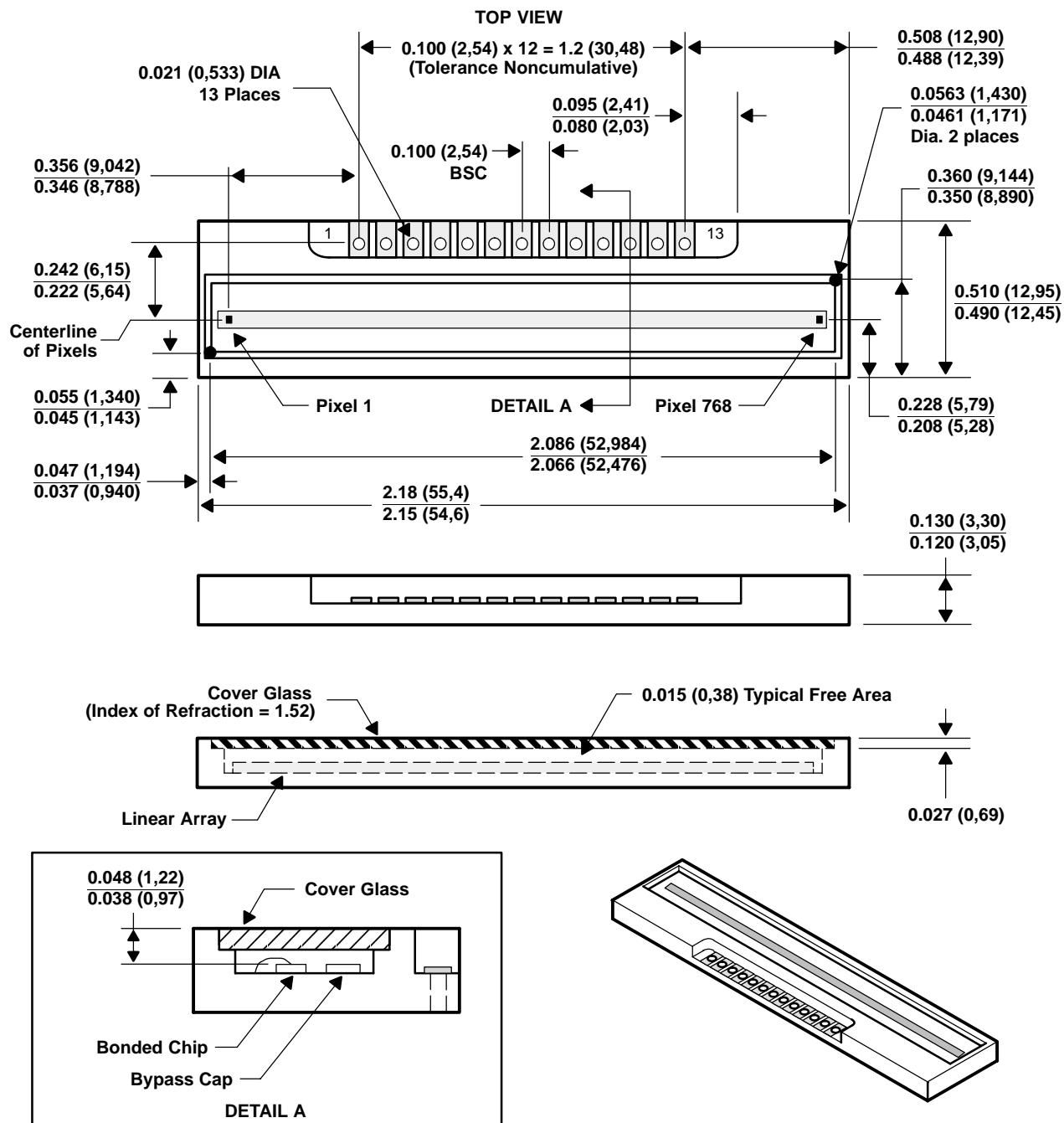


- NOTES: A. All linear dimensions are in inches (millimeters).
B. Pixel centers are located along the centerline of the mounting holes.
C. This drawing is subject to change without notice.

Figure 10. TSL1406R Mechanical Specifications

TSL1406R, TSL1406RS 768 × 1 LINEAR SENSOR ARRAY WITH HOLD

TAOS042B – MAY 2004



NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.

Figure 11. TSL1406RS Mechanical Specifications



PRODUCTION DATA — information in this document is current at publication date. Products conform to specifications in accordance with the terms of Texas Advanced Optoelectronic Solutions, Inc. standard warranty. Production processing does not necessarily include testing of all parameters.

NOTICE

Texas Advanced Optoelectronic Solutions, Inc. (TAOS) reserves the right to make changes to the products contained in this document to improve performance or for any other purpose, or to discontinue them without notice. Customers are advised to contact TAOS to obtain the latest product information before placing orders or designing TAOS products into systems.

TAOS assumes no responsibility for the use of any products or circuits described in this document or customer product design, conveys no license, either expressed or implied, under any patent or other right, and makes no representation that the circuits are free of patent infringement. TAOS further makes no claim as to the suitability of its products for any particular purpose, nor does TAOS assume any liability arising out of the use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages.

TEXAS ADVANCED OPTOELECTRONIC SOLUTIONS, INC. PRODUCTS ARE NOT DESIGNED OR INTENDED FOR USE IN CRITICAL APPLICATIONS IN WHICH THE FAILURE OR MALFUNCTION OF THE TAOS PRODUCT MAY RESULT IN PERSONAL INJURY OR DEATH. USE OF TAOS PRODUCTS IN LIFE SUPPORT SYSTEMS IS EXPRESSLY UNAUTHORIZED AND ANY SUCH USE BY A CUSTOMER IS COMPLETELY AT THE CUSTOMER'S RISK.

LUMENOLOGY, TAOS, the TAOS logo, and Texas Advanced Optoelectronic Solutions are registered trademarks of Texas Advanced Optoelectronic Solutions Incorporated.

TSL1406R, TSL1406RS

768 × 1 LINEAR SENSOR ARRAY WITH HOLD

TAOS042B – MAY 2004

